TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

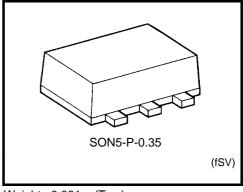
# TC7SH86FS

#### **EXCLUSIVE OR GATE**

#### **Features**

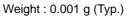
High speed:  $t_{pd}$  = 4.8 ns (typ.) at  $V_{CC}$  = 5 V Low power dissipation:  $I_{CC}$  = 2  $\mu$ A (max) at Ta = 25°C High noise immunity:  $V_{NIH}$  =  $V_{NIL}$  = 28%  $V_{CC}$  (min) 5.5V tolerant input.

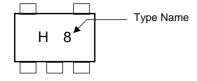
Wide operating voltage range: V<sub>CC</sub> (opr) = 2~5.5 V

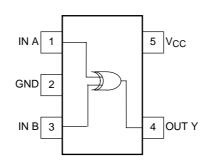


# Marking (top view)

## Pin Assignment







# **Maximum Ratings (Ta = 25°C)**

Characteristics	Symbol	Rating	Unit
Supply voltage range	Vcc	-0.5~7.0	V
DC input voltage	V <sub>IN</sub>	-0.5~7.0	V
DC output voltage	V <sub>OUT</sub>	-0.5~V <sub>CC</sub> + 0.5	V
Input diode current	lıĸ	-20	mA
Output diode current	lok	±20	mA
DC output current	lout	±25	mA
DC V <sub>CC</sub> /ground current	Icc	±50	mA
Power dissipation	PD	50	mW
Storage temperature	T <sub>stg</sub>	-65~150	°C

# **Logic Diagram**



## **Truth Table**

Α	В	Υ
L	L	L
L	Н	Н
Н	L	Н
Н	Н	L

# **Recommended Operating Conditions**

Characteristics	Symbol	Rating	Unit	
Supply voltage	V <sub>CC</sub>	2.0~5.5	V	
Input voltage	V <sub>IN</sub>	0~5.5	V	
Output voltage	V <sub>OUT</sub>	0~Vcc	V	
Operating temperature	T <sub>opr</sub>	-40~85	°C	
Input rise and fall time	dt/dv	$0 \sim 100 \text{ (V}_{CC} = 3.3 \pm 0.3 \text{ V)}$	ns/V	
Input noe and fail time	ui/uv	$0 \sim 20 \; (V_{CC} = 5 \pm 0.5 \; V)$	113/ V	

2

### **Electrical Characteristics**

#### **DC Characteristics**

Characteristics Symbol Test Circuit		Test				Ta = 25°C		Ta = -40~85°C			
		Test Condition		V <sub>CC</sub> (V)	Min	Тур.	Max	Min	Max	Unit	
High-level input VIH —				2.0	1.50	_	_	1.50	_		
	_	_			V <sub>CC</sub> × 0.7	_	_	V <sub>CC</sub> × 0.7	_	V	
Low-level input					2.0	_	_	0.50	_	0.50	V
voltage V <sub>IL</sub>	_		_	3.0~ 5.5	_	_	V <sub>CC</sub> × 0.3	_	V <sub>CC</sub> × 0.3		
			V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	Ι <sub>ΟΗ</sub> = -50 μΑ	2.0	1.9	2.0	_	1.9	_	V
					3.0	2.9	3.0	_	2.9	_	
High-level output voltage	VoH				4.5	4.4	4.5	_	4.4	_	
output remage				I <sub>OH</sub> = -4 mA	3.0	2.58	_	_	2.48	_	
				I <sub>OH</sub> = -8 mA	4.5	3.94	_	_	3.80	_	
Low-level output voltage					2.0	_	0.0	0.1	_	0.1	
	_	$V_{IN} = V_{IL}$	I <sub>OL</sub> = 50 μA	3.0	_	0.0	0.1	_	0.1	V	
				4.5	_	0.0	0.1	_	0.1		
				I <sub>OL</sub> = 4 mA	3.0	_	_	0.36	_	0.44	
				I <sub>OL</sub> = 8 mA	4.5	_	_	0.36	_	0.44	
Input leakage current	I <sub>IN</sub>	_	V <sub>IN</sub> = 5.5 V or GND			_		±0.1	_	±1.0	μА
Quiescent supply current	Icc	_	V <sub>IN</sub> = V <sub>CC</sub> o	5.5	_	_	2.0	_	20.0	μА	

3 2003-08-28

### AC Characteristics (Input: $t_r = t_f = 3 \text{ ns}$ )

Characteristics Symbol	Symbol	Test	٦	Test Condition		Ta = 25°C			Ta = -40~85°C		Unit
	Circuit		V <sub>CC</sub> (V)	C <sub>L</sub> (pF)	Min	Тур.	Max	Min	Max	Unit	
Propagation t <sub>p</sub> LH delay time t <sub>p</sub> HL		_	_	$3.3 \pm 0.3$	15		7.0	11.0	1.0	13.0	ns
	${ m t}_{ m pLH}$				50		9.5	14.5	1.0	16.5	
	$\mathrm{t}_{\mathrm{pHL}}$			5.0 ± 0.5	15	_	4.8	6.8	1.0	8.0	
					50	_	6.3	8.8	1.0	10.0	
Input capacitance	C <sub>IN</sub>	_		_			4	10	_	10	pF
Power dissipation capacitance	C <sub>PD</sub>	_			(Note)		18		_	_	pF

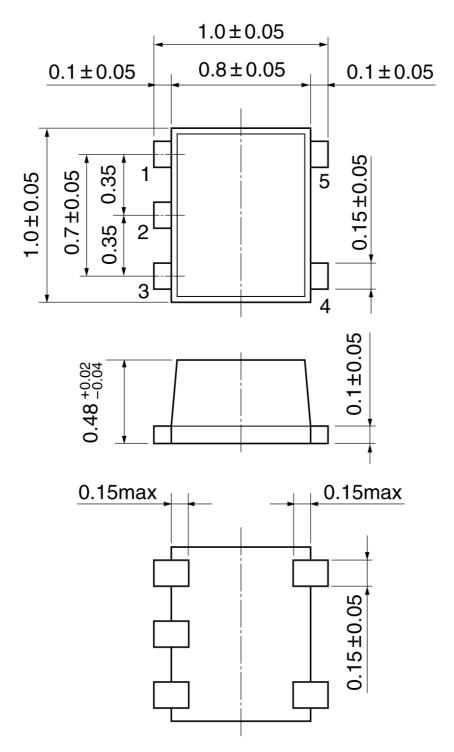
Note: C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

$$I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$$

## **Package Dimensions**

SON5-P-0.35 Unit:mm



Weight: 0.001 g (typ.)

5 2003-08-28

#### RESTRICTIONS ON PRODUCT USE

030619EBA

- The information contained herein is subject to change without notice.
- The information contained herein is presented only as a guide for the applications of our products. No
  responsibility is assumed by TOSHIBA for any infringements of patents or other rights of the third parties which
  may result from its use. No license is granted by implication or otherwise under any patent or patent rights of
  TOSHIBA or others.
- TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property.
  In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc..
- The TOSHIBA products listed in this document are intended for usage in general electronics applications (computer, personal equipment, office equipment, measuring equipment, industrial robotics, domestic appliances, etc.). These TOSHIBA products are neither intended nor warranted for usage in equipment that requires extraordinarily high quality and/or reliability or a malfunction or failure of which may cause loss of human life or bodily injury ("Unintended Usage"). Unintended Usage include atomic energy control instruments, airplane or spaceship instruments, transportation instruments, traffic signal instruments, combustion control instruments, medical instruments, all types of safety devices, etc.. Unintended Usage of TOSHIBA products listed in this document shall be made at the customer's own risk.
- The products described in this document are subject to the foreign exchange and foreign trade laws.
- TOSHIBA products should not be embedded to the downstream products which are prohibited to be produced and sold, under any law and regulations.